If the Examiner in charge of this case feels that there are any remaining unresolved issues in this case, the Examiner is urged to call the undersigned attorney at the below listed telephone number which is in the Pacific Coast Time Zone.

Respectfully Submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Specification:

The paragraph beginning at page 1, line 4 (as amended in the Preliminary Amendment dated February 12, 2001), has been amended as follows:

--This application is a continuation of U.S. Patent Application Serial Number 09/259,982 filed March 1, 1999, and now issued as U.S. Patent 6,207,392 as a continuation in part of U.S. Patent Application Serial Number 08/978,450 filed November 25, 1997, and now issued as U.S. Patent 5,990,479.--

The paragraph beginning at line 24 of page 11, has been amended as follows:

Formation of nanometer crystals of Group III-V semiconductors is described in copending and commonly assigned Alivisatos et al. U.S. Patent 5,751,018 ~~5,571,018~~; Alivisatos et al. U.S. Patent 5,505,928; and Alivisatos et al. U.S. Patent 5,262,357, which also describe ~~describes~~ the formation of Group II-VI semiconductor nanocrystals, and which are ~~is~~ also assigned to the assignee of this invention. Also described therein is the control of the size of the semiconductor nanocrystals during formation using crystal growth terminators. The teachings of Alivisatos et al. U.S. Patent 5,751,018 ~~5,571,018~~, and Alivisatos et al. U.S. Patent 5,262,357 are each hereby specifically incorporated by reference.

In the Claims:

159. (Amended) The process for treating a material of claim 158, wherein each of said two or more semiconductor nanocrystal probes comprises:

(a) ~~(α)~~ a semiconductor nanocrystal capable of providing a second energy that is the same as that of the semiconductor nanocrystals of which the others of said two or more semiconductor nanocrystal probes are comprised;

(b) ~~(β)~~ a semiconductor nanocrystal capable of providing a second energy that is distinguishable from that of the semiconductor nanocrystals of which at least one of the others of said two or more semiconductor nanocrystal probes are comprised; or

(c) ~~(γ)~~ a combination of semiconductor nanocrystals capable of providing a second energy that is the same as or that is distinguishable from that of the semiconductor nanocrystals of which at least one of the others of said two or more semiconductor nanocrystal probes are comprised.

174. (Amended) The process for treating a material of claim 173 ~~172~~, wherein said two or more substructures each comprise one layer in a layered structure.

177. The process for treating a material of claim 176 ~~175~~, wherein each of said one or more affinity molecules comprises a molecule of one or more strands of nucleic acid.

178. The process for treating a material of claim 177 ~~176~~, wherein each of said one or more detectable substances comprises a molecule of one or more strands of nucleic acid with which said probe bonds.

179. The process for treating a material of claim 176 ~~175~~, wherein each of said one or more affinity molecules comprises a protein.

180. The process for treating a material of claim 179 ~~178~~, wherein the protein is an antibody.